S-104.3610 Nanotechnology (5 cr)

Exam 24.5.2011

Please answer either in English or Finnish.

- 1. Explain briefly (max. 2 pages altogether, draw schematics if needed):
 - a) extreme ultraviolet (EUV) lithography
 - b) phase-shift mask in optical lithography
 - c) break-junction technique in molecular electronics
 - d) nanocomposites
 - e) principle of a read head of magnetic disk drive (GMR effect)
 - f) superhydrophobic surfaces (each 1 p)
- 2. Nanoimprint lithography and comparison to other nanolithography techniques. (6 p)
- 3. Structure, fabrication and properties of graphene. (6 p)
- 4. a) Atomic layer deposition (ALD). (3 p)
 - b) Three examples of biomimetics (3 p)
- 5. a) Structure and basic operation principle of a single electron transistor (SET). (3 p)
 - b) Effect of surface charge and Debye length in nanofluidics. (3 p)